



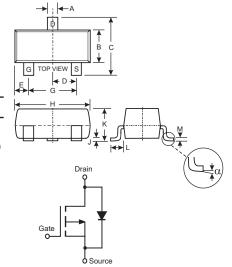
P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish).
- Terminal Connections: See Diagram
- Marking (See Page 2): K84
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approximate)



	SOT-23										
Dim	Min	Max									
Α	0.37	0.51									
В	1.20	1.40									
С	2.30	2.50									
D	0.89	1.03									
E	0.45	0.60									
G	1.78	2.05									
Н	2.80	3.00									
J	0.013	0.10									
K	0.903	1.10									
L	0.45	0.61									
M	0.085	0.180									
α	0°	8°									
All Din	All Dimensions in mm										

Maximum Ratings @ $T_A = 25$ °C unless otherwise specified

eristic		Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	-50	V	
Drain-Gate Voltage $R_{GS} \le 20 K\Omega$		V_{DGR}	-50	V	
Gate-Source Voltage	ate-Source Voltage Continuous		±20	V	
Drain Current (Note 1) Continuous		I _D	-130	mA	
Total Power Dissipation (Note 1)		P _d	300	mW	
Thermal Resistance, Junction to Ambient		$R_{ hetaJA}$	417	°C/W	
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C	

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)	'					
Drain-Source Breakdown Voltage		-50	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_		-15 -60 -100	μA μA nA	V _{DS} = -50V, V _{GS} = 0V, T _J = 25°C V _{DS} = -50V, V _{GS} = 0V, T _J = 125°C V _{DS} = -25V, V _{GS} = 0V, T _J = 25°C
Gate-Body Leakage	I _{GSS}	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(th)}	-0.8	_	-2.0	V	$V_{DS} = V_{GS}$, $I_D = -1mA$
Static Drain-Source On-Resistance	R _{DS (ON)}	_	_	10	Ω	$V_{GS} = -5V, I_D = -0.100A$
Forward Transconductance	g _{FS}	0.05	_	_	S	$V_{DS} = -25V, I_{D} = -0.1A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	_	_	45	pF	
Output Capacitance	Coss	_	_	25	pF	$V_{DS} = -25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	_	12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	_	10	_	ns	$V_{DD} = -30V, I_D = -0.27A,$
Turn-Off Delay Time	t _{D(OFF)}	_	18	_	ns	$R_{GEN} = 50\Omega$, $V_{GS} = -10V$

Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

- 2. Short duration test pulse used to minimize self-heating effect.
- 3. No purposefully added lead.

BSS84

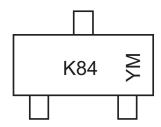


Ordering Information (Note 4)

查询"BSS84-7-F b供应 商	Packaging	Shipping		
BSS84-7-F	SOT-23	3000/Tape & Reel		

Notes: 4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



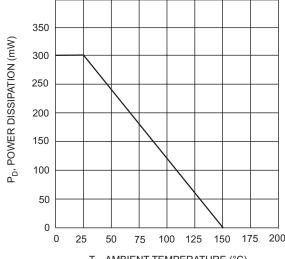
K84 = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002

M = Month ex: 9 = September

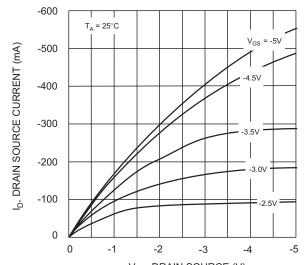
Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	М	N	Р	R	S	Т	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



T_A, AMBIENT TEMPERATURE (°C) Fig. 1, Max Power Dissipation vs Ambient Temperature



V_{DS}, DRAIN SOURCE (V) Fig. 2, Drain Source Current vs. Drain Source Voltage



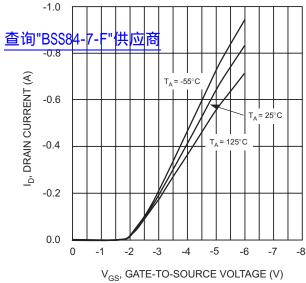
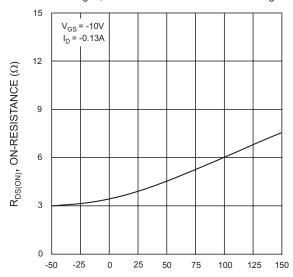
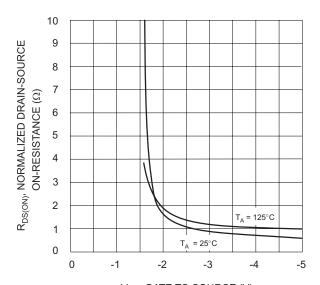


Fig. 3, Drain Current vs. Gate Source Voltage



T_J, JUNCTION TEMPERATURE (°C) Fig. 5, On-Resistance vs. Junction Temperature



V_{GS}, GATE TO SOURCE (V) Fig. 4, On Resistance vs. Gate Source Voltage

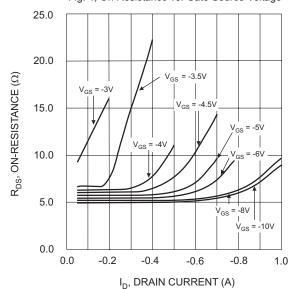


Fig. 6, On-Resistance vs. Drain Current

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